

Regulated 5V Charge Pump

PRODUCT SUMMARY

Input voltage range: 2.7V to 5.0V
 Regulated output voltage of 5V \pm 4%
 Output current: 100mA ($V_{IN} = 3.3V$)
 110mA ($V_{IN} = 3.6V$)

FEATURES

Ultralow power: $I_{IN} = 13\mu A$
 No inductors needed
 Very low shutdown current: $<1\mu A$
 Internal oscillator: 650KHz
 Short-circuit and over-temperature protection

APPLICATIONS

White or Blue LED Backlighting
 SIM Interface Supplies for Cellular Telephones
 Li-Ion Battery Backup Supplies
 Local 3V to 5V Conversion
 Smart Card Readers
 PCMCIA Local 5V Supplies

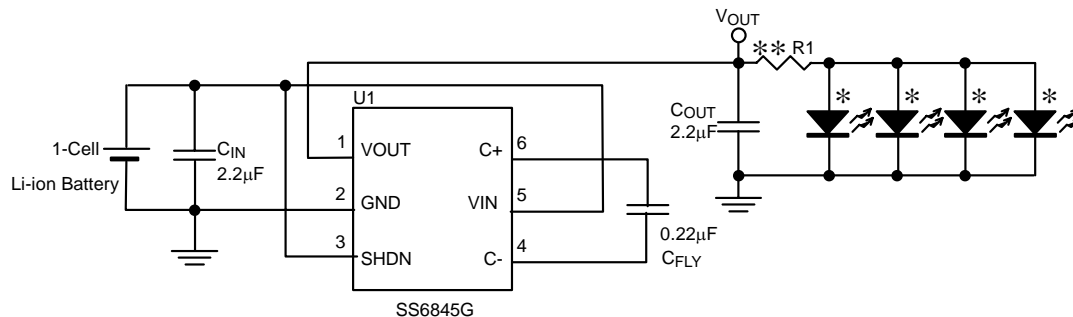
 **Pb-free; RoHS-compliant SOT-23-6 package**

DESCRIPTION

The SS6845G is a micropower charge pump DC/DC converter that produces a regulated 5V output. The input voltage range is 2.7V to 5.0V. Extremely low operating current (13 μA typical with no load) and a low external part count (one 0.22 μF flying capacitor and two small bypass capacitors at the input and output) make the SS6845G ideally suitable for small, battery-powered applications.

The SS6845G operates as a PSM-mode (Pulse Skipping Modulation) switched capacitor voltage doubler to produce a regulated output and features thermal shutdown capability and short circuit protection.

TYPICAL APPLICATION CIRCUIT



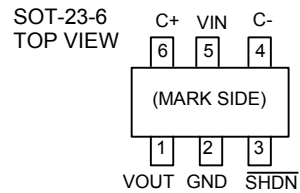
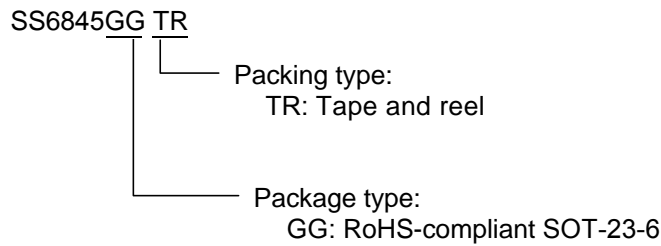
Regulated 5V Output from 2.7V to 5.0V Input

* WLED series number: NSPW310BS, $V_F = 3.6V$, $I_F = 20mA$

** $R1 = \frac{V_{OUT} - V_F}{I_F \times N_{WLED}}$, where N_{WLED} is the number of WLEDs.

C_{IN} , C_{OUT} : CELMK212BJ225MG (X5R) (0805), TAIYO YUDEN

C_{FLY} : CEEMK212BJ224KG (X7R) (0805), TAIYO YUDEN

ORDERING INFORMATION
PIN CONFIGURATION

SOT-23-6 Marking

| Part No. | Marking |
|----------|---------|
| SS6845GG | BO50P |

ABSOLUTE MAXIMUM RATINGS

| | |
|---|-----------------|
| VIN to GND | 6V |
| VOUT to GND | 6V |
| All other ins to GND | 6V |
| VOUT short-circuit duration | Continuous |
| Operating ambient temperature range | -40°C to 85 °C |
| Junction temperature | 125°C |
| Storage temperature range | -65°C to 150 °C |
| Lead temperature (minimum 10 seconds) | 260°C |

Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

TEST CIRCUIT

Refer to the TYPICAL APPLICATION CIRCUIT on page 1.

ELECTRICAL CHARACTERISTICS

($T_A=25^{\circ}\text{C}$, $C_{\text{FLY}}=0.22\mu\text{F}$, $C_{\text{IN}}=2.2\mu\text{F}$, $C_{\text{OUT}}=2.2\mu\text{F}$, unless otherwise specified.) (Note 1)

| PARAMETER | TEST CONDITIONS | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|---------------------------------|--|------------------------------|------|------|------|---------------|
| Input voltage | | V_{IN} | 2.7 | | 5.0 | V |
| Output voltage | $2.7\text{V} \leq V_{\text{IN}} < 3.3\text{V}$, $I_{\text{OUT}} \leq 30\text{mA}$ | V_{OUT} | 4.8 | 5.0 | 5.2 | V |
| | $3.3\text{V} \leq V_{\text{IN}} \leq 5.0\text{V}$, $I_{\text{OUT}} \leq 60\text{mA}$ | | 4.8 | 5.0 | 5.2 | |
| Continuous output current | $V_{\text{IN}}=3\text{V}$, $V_{\text{OUT}}=5.0\text{V}$ $\overline{\text{SHDN}}=V_{\text{IN}}$ | I_{OUT} | 60 | | | mA |
| Supply current | $2.7\text{V} \leq V_{\text{IN}} \leq 5.0\text{V}$, $I_{\text{OUT}}=0$, $\overline{\text{SHDN}}=V_{\text{IN}}$ | I_{CC} | | 13 | 30 | μA |
| Shutdown current | $2.7\text{V} \leq V_{\text{IN}} \leq 5.0\text{V}$, $I_{\text{OUT}}=0$, $\overline{\text{SHDN}}=0\text{V}$ | $I_{\overline{\text{SHDN}}}$ | | 0.01 | 1.0 | μA |
| Output ripple | $V_{\text{IN}}=3\text{V}$, $I_{\text{OUT}}=50\text{mA}$ | V_{R} | | 60 | | mV |
| Efficiency | $V_{\text{IN}}=2.7\text{V}$, $I_{\text{OUT}}=30\text{mA}$ | η | | 83 | | % |
| Switching frequency | Oscillator free-running | f_{OSC} | | 650 | | KHz |
| Shutdown input threshold (High) | | V_{IH} | 1.4 | | | V |
| Shutdown input threshold (Low) | | V_{IL} | | | 0.3 | V |
| Shutdown input current (High) | $\overline{\text{SHDN}}=V_{\text{IN}}$ | I_{IH} | -1 | | 1 | μA |
| Shutdown input current (Low) | $\overline{\text{SHDN}}=0\text{V}$ | I_{IL} | -1 | | 1 | μA |
| Vout turn-on time | $V_{\text{IN}}=3\text{V}$, $I_{\text{OUT}}=0\text{mA}$ | t_{ON} | | 0.5 | | mS |
| Output short-circuit current | $V_{\text{IN}}=3\text{V}$, $V_{\text{OUT}}=0\text{V}$, $\overline{\text{SHDN}}=V_{\text{IN}}$ | I_{SC} | | 170 | | mA |

Note1: Specifications are production tested at $T_A=25^{\circ}\text{C}$. Specifications over the -40°C to 85°C operating temperature range are assured by design, characterization and correlation with Statistical Quality Controls (SQC).

TYPICAL PERFORMANCE CHARACTERISTICS

(C_N , C_{OUT} : CELMK212BJ225MG, C_{FLY} : CEEMK212BJ224KG)

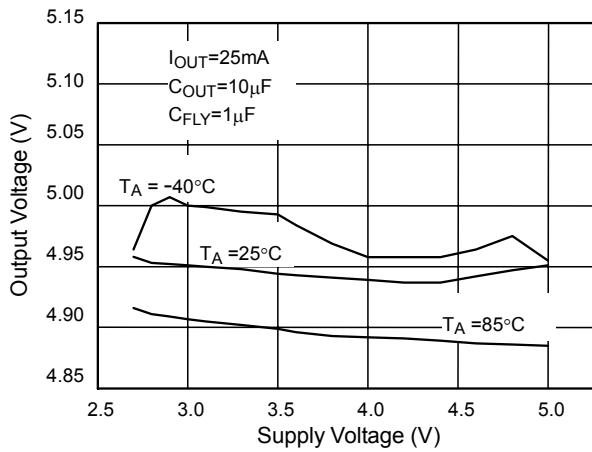


Fig. 1 Line Regulation

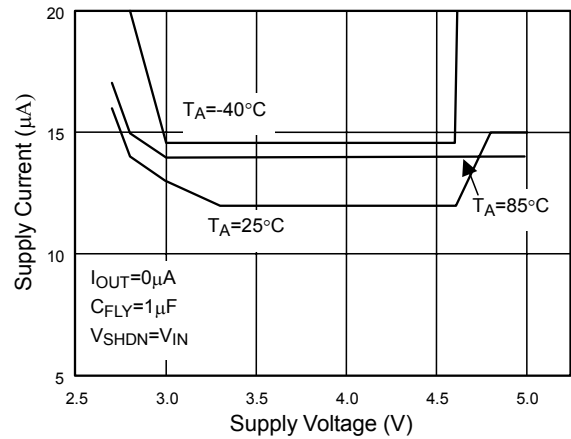


Fig. 2 No Load Supply Current vs. Supply Voltage

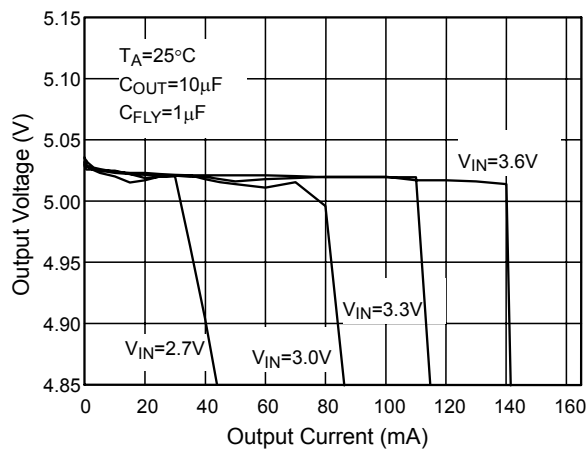


Fig. 3 Load Regulation

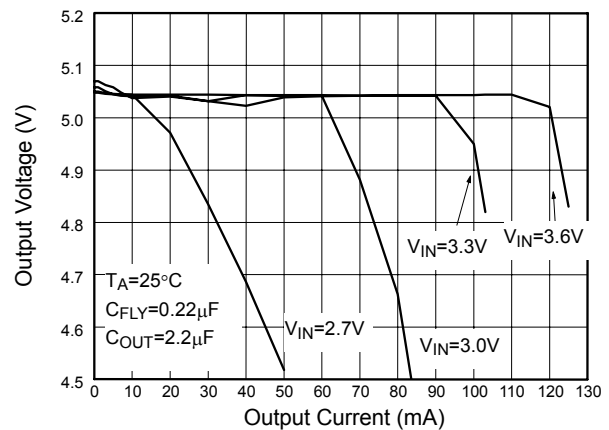


Fig. 4 Load Regulation

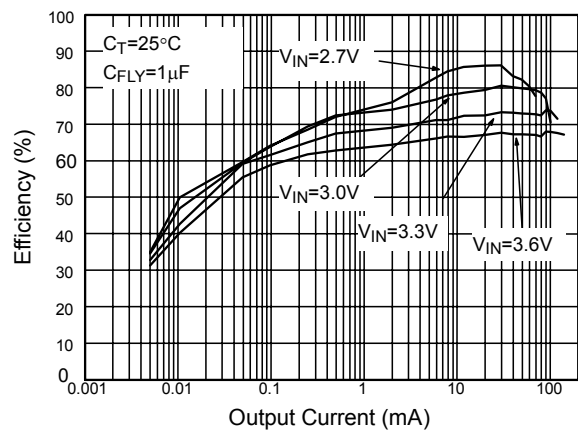


Fig. 5 Efficiency

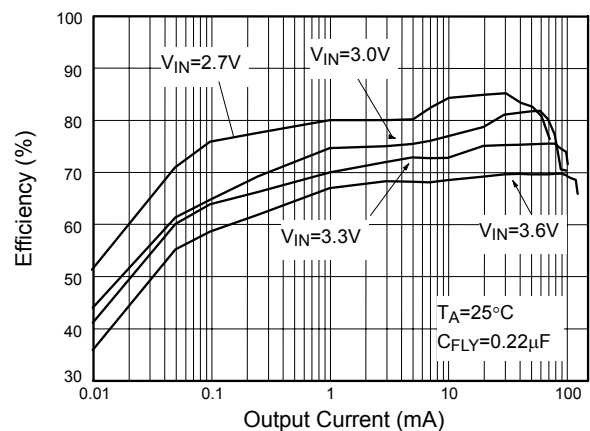


Fig. 6 Efficiency

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

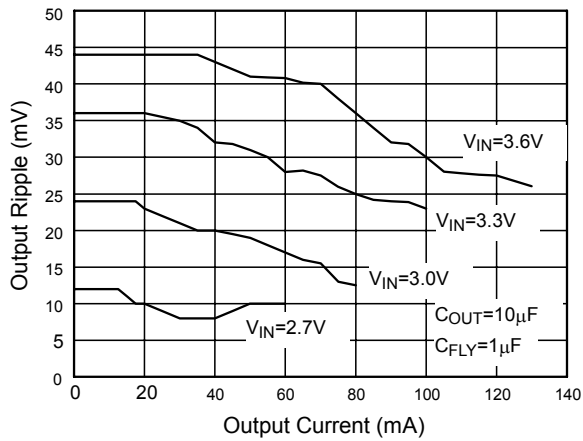


Fig. 7 Output Current vs. Output Ripple

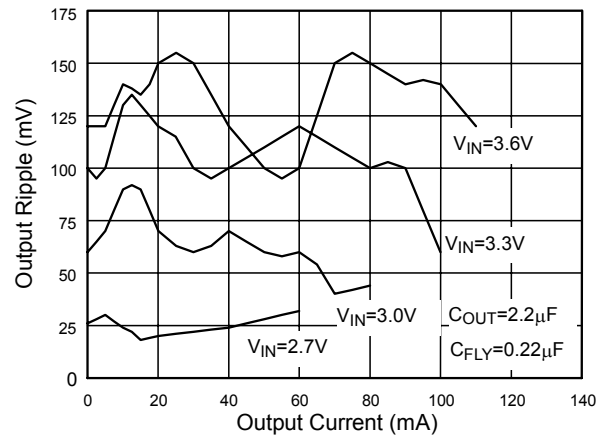


Fig. 8 Output Current vs. Output Ripple

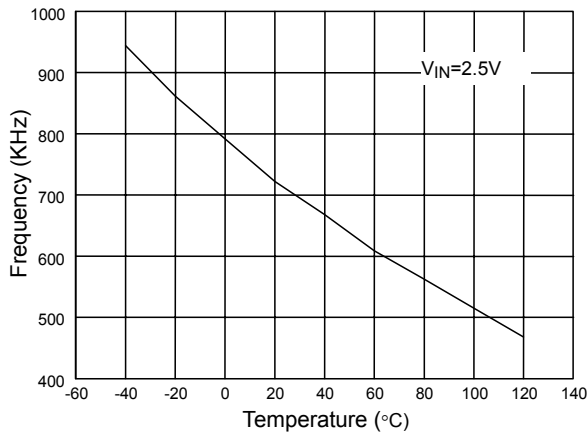


Fig. 9 Frequency vs. Temperature

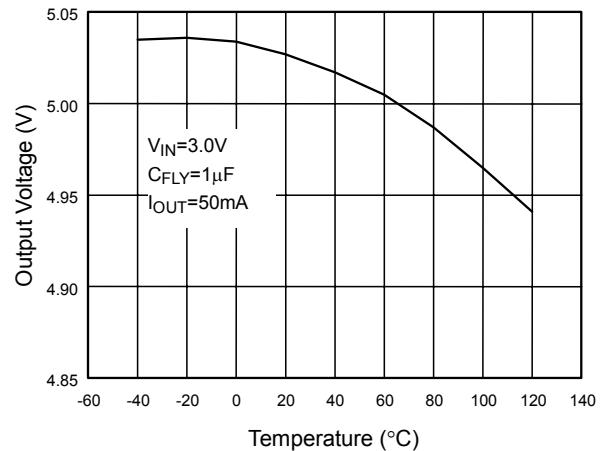


Fig. 10 Output Voltage vs. Temperature

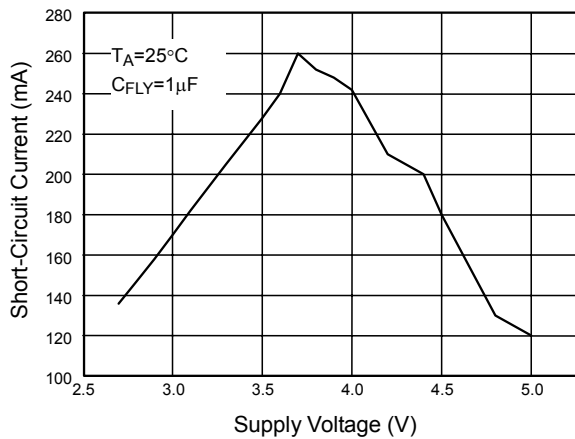


Fig. 11 Short-Circuit Current vs. Supply Voltage

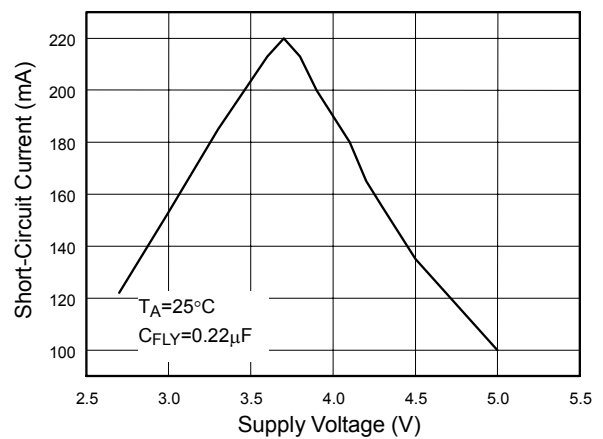
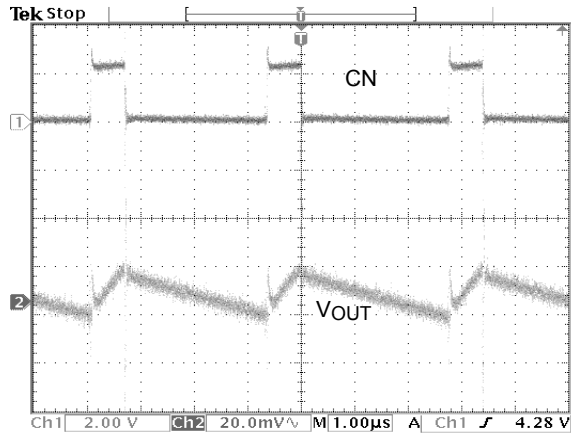
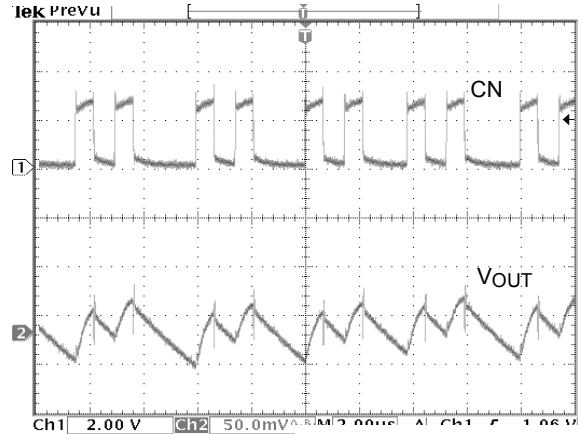
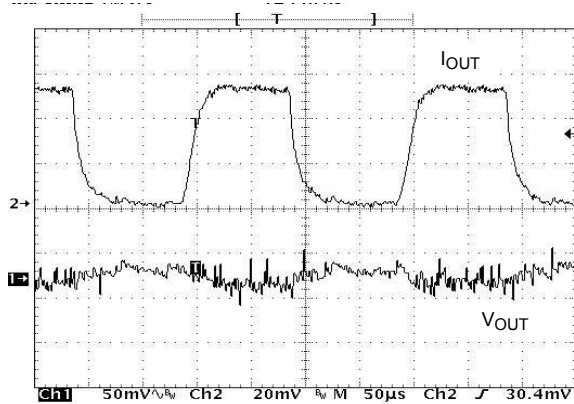
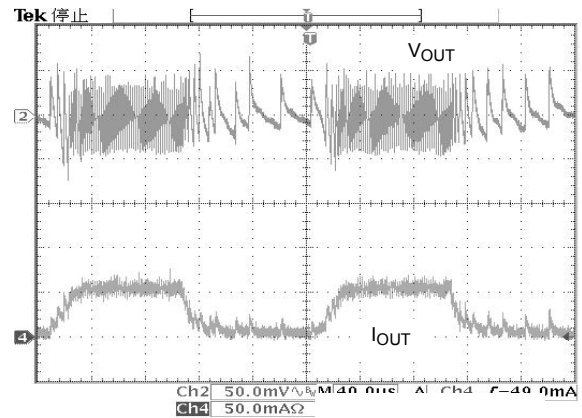
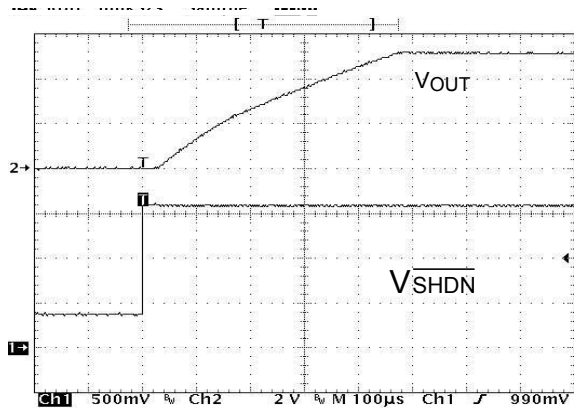
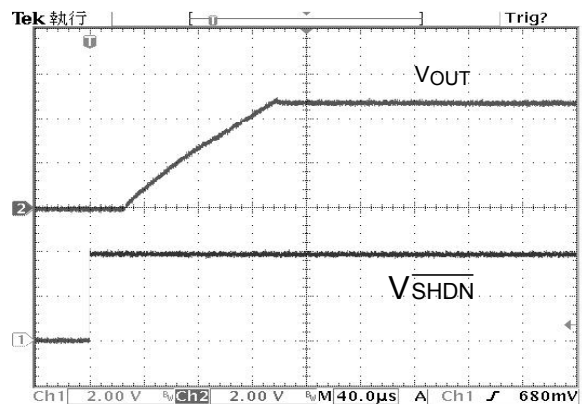
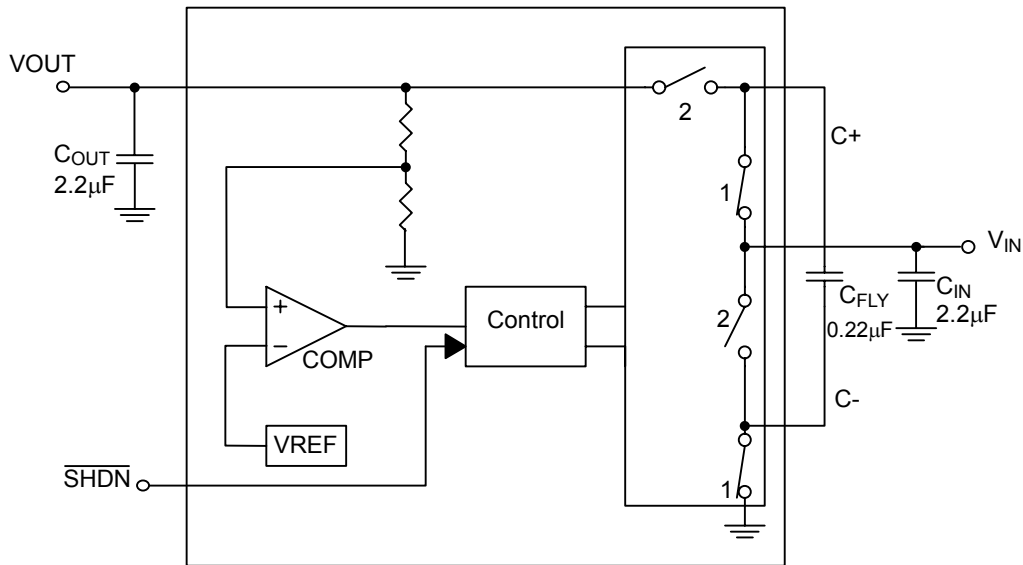


Fig. 12 Short-Circuit Current vs. Supply Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

Fig. 13 Output Ripple
 $V_{IN}=3.0V, I_{OUT}=50mA, C_{OUT}=10\mu F, C_{FLY}=1\mu F$

Fig. 14 Output Ripple
 $V_{IN}=3.0V, I_{OUT}=50mA, C_{OUT}=2.2\mu F, C_{FLY}=0.22\mu F$

Fig. 15 Load Transient Response
 $V_{IN}=3.0V, I_{OUT}=0mA\sim 50mA, C_{OUT}=10\mu F, C_{FLY}=1\mu F$

Fig. 16 Load Transient Response
 $V_{IN}=3.0V, I_{OUT}=0mA\sim 50mA, C_{OUT}=2.2\mu F, C_{FLY}=0.22\mu F$

Fig. 17 Start-Up Time
 $V_{IN}=3.0V, I_{OUT}=0A, C_{OUT}=10\mu F$

Fig. 18 Start-Up Time
 $V_{IN}=3.0V, I_{OUT}=0A, C_{OUT}=2.2\mu F$

BLOCK DIAGRAM



PIN DESCRIPTIONS

- | | |
|---|--|
| <p>PIN 1: VOUT - Regulated output voltage. For the best performance, V_{OUT} should be bypassed with a 2.2µF (min) low ESR capacitor with the shortest possible leads.</p> <p>PIN 2: GND - Ground. Should be tied to a ground plane for best performance.</p> <p>PIN 3: $\overline{\text{SHDN}}$ - Active-low shutdown input. A low voltage on $\overline{\text{SHDN}}$ disables the SS6845G. $\overline{\text{SHDN}}$ is not allowed to float.</p> | <p>PIN 4: C- - Flying capacitor negative terminal.</p> <p>PIN 5: VIN - Input supply voltage. V_{IN} should be bypassed with a 2.2µF (min) low ESR capacitor.</p> <p>PIN 6: C+ - Flying capacitor positive terminal.</p> |
|---|--|

APPLICATION INFORMATION

Introduction

The SS6845G is a micropower charge pump DC/DC converter that produces a regulated 5V output with an input voltage range from 2.7V to 5.0V. It utilizes the charge pump topology to boost V_{IN} to a regulated output voltage. Regulation is obtained by sensing the output voltage through an internal resistor divider. A switched doubling circuit enables the charge pump when the feedback voltage is lower than the trip point of the internal comparator, and vice versa. When the charge pump is enabled, a two-phase non-overlapping clock activates the charge pump switches. To maximize battery life for a battery-use application, quiescent current is limited to no more than 13 μ A.

Operation

This kind of converter uses capacitors to store and transfer energy. Since the capacitors can't change their voltage level abruptly, the voltage ratio of V_{OUT} over V_{IN} is limited to some range. Capacitive voltage conversion is obtained by switching a capacitor periodically. It first charges the capacitor by connecting it across a voltage source and then connects it to the output. Referring to Fig. 19, during the on state of internal clock, Q_1 and Q_4 are closed, which charges C_1 to V_{IN} level. During the off state, Q_3 and Q_2 are closed. The output voltage is V_{IN} plus V_{C1} , that is, $2V_{IN}$.

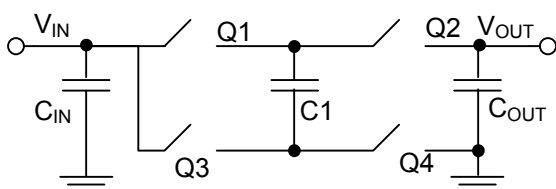


Fig. 19 The circuit of charge pump

Short Circuit/Thermal Protection

The SS6845G includes built-in short circuit current limiting as well as over-temperature protection. During a short circuit condition, the output current is automatically constrained to approximately 170mA. This short circuit current will cause a rise in the internal IC junction temperature. When the die temperature exceeds 150°C, the thermal protection will shut down the charge pump switching operation and the die temperature will then reduce. Once the die temperature drops below 135°C, the charge pump switching circuit will restart. If the fault has not been eliminated, the this protection mechanism will repeat again and again, allowing the SS6845G to work continuously in a short circuit condition without damaging the device.

Shutdown

In shutdown mode, the output is disconnected from the input. The input current is extremely low since most of the circuitry is turned off. Due to high impedance, the shutdown pin cannot float.

Efficiency

The diagrams, Fig. 20 and Fig. 21 show the operation of the charge pump in the on and off states.

R_{DS-ON} is the resistance of the switching element during conduction. ESR is the equivalent series resistance of the flying capacitor C_1 . I_{ON-AVE} and $I_{OFF-AVE}$ are the average current during the on-state and off-state, respectively. D is the duty-cycle, which means the ratio of the on-state time to the total cycle time. Let's look at capacitor C_1 - assuming that capacitor C_1 , has reached its steady state, then the amount of charge flowing into C_1 during the on-state is equal to that flowing out of C_1 during the off-state.

2. **Package Size:** A ceramic capacitor with large volume (0805), gets a lower ESR than a small one (0603). Therefore, larger devices provide improved transient response over smaller ones.

Table 1 lists the recommended components for use with the SS6845G.

Table.1 Bill of Material

| Designator | Part Type | Description | Vendor |
|------------------|-----------|------------------------|----------------|
| C _{IN} | 2.2μ | CELMK212BJ-225MG (X5R) | TAIYO YUDEN |
| C _{FLY} | 0.22μ | CEEMK212BJ-224KG (X7R) | TAIYO YUDEN |
| C _{OUT} | 2.2μ | CELMK212BJ-225MG (X5R) | TAIYO YUDEN |

Power Dissipation

Now, let's look at the power dissipation in R_{DS-ON} and ESR. Assume that the R_{DS-ON} of each internal switching element in the SS6845G is equal and ESR is the equivalent series resistance of C_{FLY} (refer to Fig. 20 and Fig. 21). The approximation of the power losses of R_{DS-ON} and ESR are given below:

$$\begin{aligned}
 P_{R_{DS-ON}} &\cong I_{ON-AVE}^2 \times 2R_{DS-ON} \times D + I_{OFF-AVE}^2 \times 2R_{DS-ON} \times (1-D) \\
 &= \left(\frac{I_{IN}}{2D}\right)^2 \times 2R_{DS-ON} \times D + \left(\frac{I_{OUT}}{1-D}\right)^2 \times 2R_{DS-ON} \times (1-D) \\
 &= \left(\frac{2I_{OUT}}{2D}\right)^2 \times 2R_{DS-ON} \times D + \left(\frac{I_{OUT}}{1-D}\right)^2 \times 2R_{DS-ON} \times (1-D) \\
 &= I_{OUT}^2 \times \left(\frac{2}{D}R_{DS-ON}\right) + I_{OUT}^2 \times \left(\frac{2}{1-D}R_{DS-ON}\right) \\
 &= I_{OUT}^2 \times \frac{2}{D(1-D)} \times R_{DS-ON} \\
 &\dots\dots\dots(7)
 \end{aligned}$$

$$\begin{aligned}
 P_{ESR} &\cong I_{ON-AVE}^2 \times ESR \times D + I_{OFF-AVE}^2 \times ESR \times (1-D) \\
 &= \left(\frac{I_{IN}}{2D}\right)^2 \times ESR \times D + \left(\frac{I_{OUT}}{1-D}\right)^2 \times ESR \times (1-D) \\
 &= I_{OUT}^2 \times ESR \times \frac{1}{D} + I_{OUT}^2 \times ESR \times \frac{1}{1-D} \\
 &= I_{OUT}^2 \times ESR \times \frac{1}{D(1-D)}
 \end{aligned}$$

With a duty-cycle of 0.5, the power loss of R_{DS-ON} is

$$\begin{aligned}
 P_{R_{DS-ON}} &\cong I_{OUT}^2 \times \frac{2}{0.5(1-0.5)} \times R_{DS-ON} \\
 &= I_{OUT}^2 \times 8R_{DS-ON}
 \end{aligned}$$

$$\begin{aligned}
 P_{ESR} &\cong I_{OUT}^2 \times ESR \times \frac{1}{0.5(1-0.5)} \\
 &= I_{OUT}^2 \times 4ESR
 \end{aligned}$$

In fact, whether the current is the on-state or the off-state, it decays exponentially rather than flows steadily, and as the root mean square value of exponential decay is not equal to that of steady flow, then we must use an approximation.

Let's use another approach to look at the charge pump circuit and focus on the flying capacitor C₁. Referring to Fig. 20, when the circuit is in the on state, the voltage across C₁ is:

$$V_{C-ON}(t) = V_{IN} - 2R_{DS-ON} \times I_{ON}(t) - ESR \times I_{ON}(t) \dots(9)$$

The average of V_{C1} during the on-state is:

$$V_{C-ON-AVE} = V_{IN} - 2R_{DS-ON} \times I_{ON-AVE} - ESR \times I_{ON-AVE} \dots\dots\dots(10)$$

Similarly, referring to Fig. 21, when the circuit is in the off-state, the voltage of C₁ is:

$$\begin{aligned}
 V_{C-OFF}(t) &= \\
 &V_{OUT} - V_{IN} + 2R_{DS-ON} \times I_{OFF}(t) + ESR \times I_{OFF}(t) \\
 &\dots\dots\dots(11)
 \end{aligned}$$

The average of V_{C1} during the off-state is:

$$\begin{aligned}
 V_{C-OFF-AVE} &= \\
 &V_{OUT} - V_{IN} + 2R_{DS-ON} \times I_{OFF-AVE} + ESR \times I_{OFF-AVE} \\
 &\dots\dots\dots(12)
 \end{aligned}$$

The difference in charge stored in C₁ between the on-state and off-state is the net charge transferred to the output in one cycle.

$$\begin{aligned}
 \Delta Q &= Q_{ON} - Q_{OFF} \\
 &= C_1 \times (V_{C1-ON-AVE} - V_{C1-OFF-AVE}) \\
 &= C_1 \times (2V_{IN} - V_{OUT} - 2R_{DS-ON} \times I_{ON-AVE} - 2R_{DS-ON} \times I_{OFF-AVE} - ESR \times I_{ON-AVE} - ESR \times I_{OFF-AVE}) \dots\dots\dots(13) \\
 &= C_1 \times (2V_{IN} - V_{OUT} - 2R_{DS-ON} \times \frac{I_{OUT}}{D} - 2R_{DS-ON} \times \frac{I_{OUT}}{1-D} - ESR \times \frac{I_{OUT}}{D} - ESR \times \frac{I_{OUT}}{1-D}) \\
 &= C_1 \times [2V_{IN} - V_{OUT} - (2R_{DS-ON} + ESR) \times I_{OUT} \times \frac{1}{D(1-D)}]
 \end{aligned}$$

Thus the output current can be written as

$$\begin{aligned}
 I_{OUT} &= f \times \Delta Q = f \times (Q_{ON} - Q_{OFF}) \\
 &= f \times C_1 \times [2V_{IN} - V_{OUT} - (2R_{DS-ON} + ESR) \times I_{OUT} \times \frac{1}{D(1-D)}] \dots\dots\dots(14)
 \end{aligned}$$

When the duty cycle is 0.5, the output current can be written as:

$$\begin{aligned}
 I_{OUT} &= f \times C_1 \times [2V_{IN} - V_{OUT} - (2R_{DS-ON} + ESR) \times I_{OUT} \times \frac{1}{0.5(1-0.5)}] \dots\dots\dots(15) \\
 &= fC_1 \times [2V_{IN} - V_{OUT} - (8R_{DS-ON} + 4ESR) \times I_{OUT}]
 \end{aligned}$$

And equation (15) can be re-written as:

$$2V_{IN} - V_{OUT} = \frac{1}{fC_1} \times I_{OUT} + (8R_{DS-ON} + 4ESR) \times I_{OUT} \dots\dots\dots(16)$$

According to equation (16), when the duty cycle is 0.5, the equivalent circuit of the charge pump is shown in Fig. 22. The term $8R_{DS-ON}$ is the total effect of switching resistance, $1/fC_1$ is the effect of flying capacitor and $4ESR$ is its equivalent resistance.

From the equivalent circuit shown in Fig. 22, it is seen that the terms $1/fC_1$, $4ESR$ and $8R_{DS-ON}$ should be as small as possible to get large output current. However, since the R_{DS-ON} is internal to the SS6845G, all that can be done is to lower the values of $1/fC_1$ and ESR . However even if the values of $1/fC_1$ and ESR can be kept as small as possible, the term $8R_{DS-ON}$ still dominates the limit of the maximum output current.

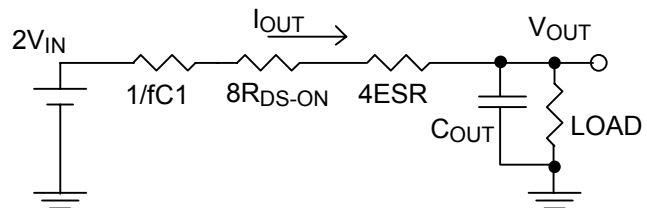


Fig. 22 The equivalent circuit of charge pump

Layout Considerations

With the high switching frequency and transient currents of the SS6845G, careful consideration of PCB layout is important. To achieve the best performance, it is necessary to minimize the distance between every component and also to minimize the length of every connection and maximize the trace width. Make sure each device connects to an immediate ground plane. Fig. 23 to Fig. 25 show a recommended layout.

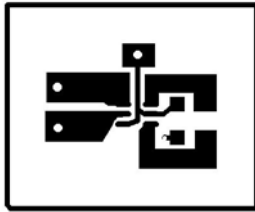


Fig. 23 Top layer

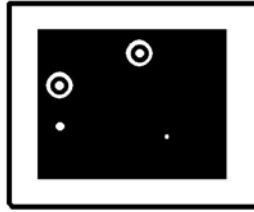


Fig. 24 Bottom layer

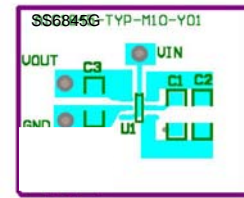
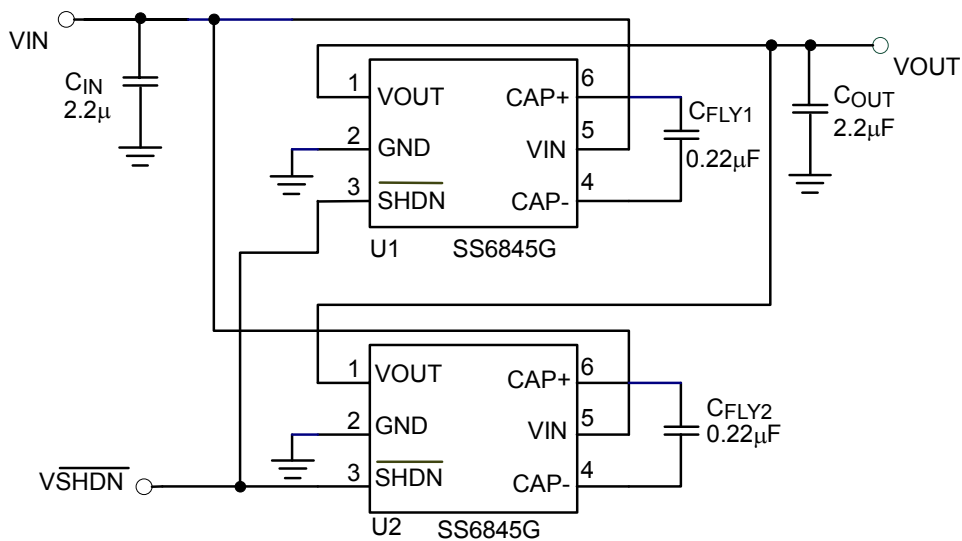


Fig. 25 Topover layer

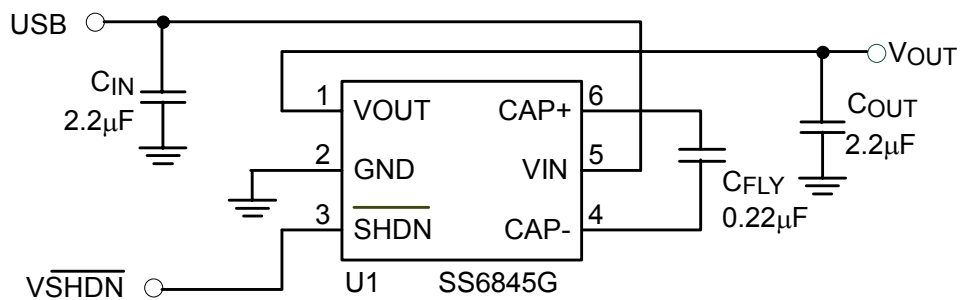
APPLICATION EXAMPLES



C_{IN} , C_{OUT} : TAIYO YUDEN Ceramic Capacitor, CELMK212BJ225MG (X5R) (0805)

C_{FLY1} , C_{FLY2} : TAIYO YUDEN Ceramic Capacitor, CEEMK212BJ224KG (X7R) (0805)

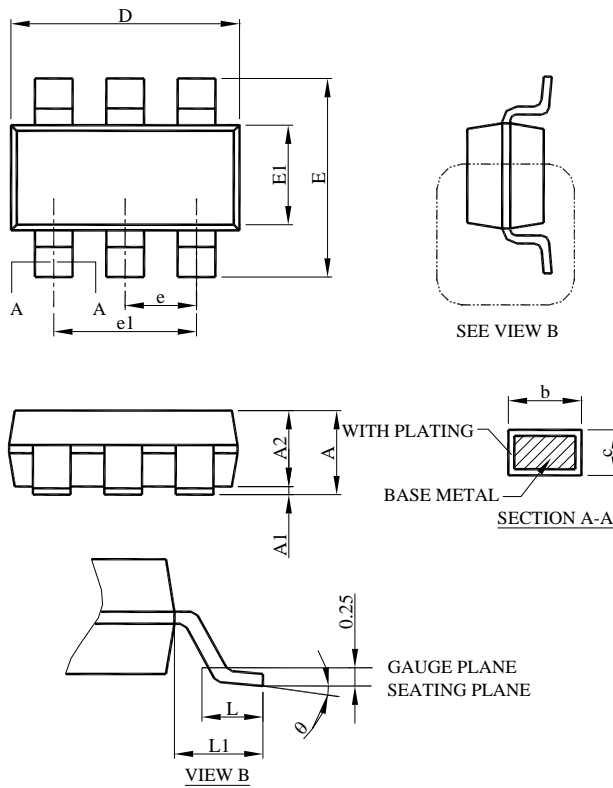
Fig. 26 Using two SS6845G in parallel to provide larger output current.



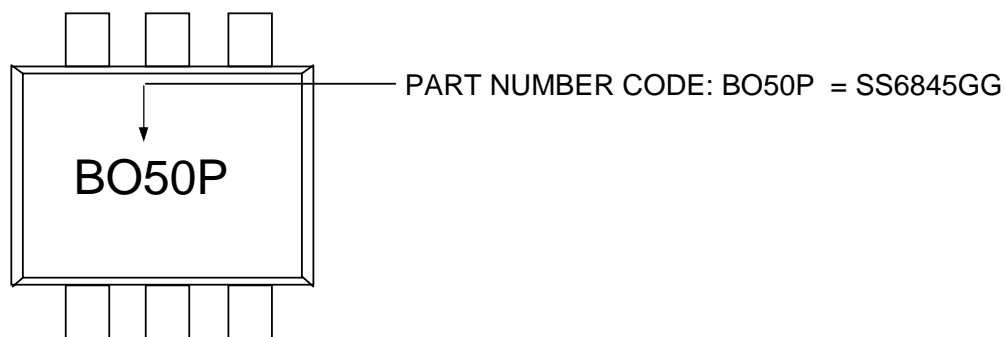
C_{IN} , C_{OUT} : TAIYO YUDEN Ceramic Capacitor, CELMK212BJ225MG (X5R) (0805)

C_{FLY1} : TAIYO YUDEN Ceramic Capacitor, CEEMK212BJ224KG (X7R) (0805)

Fig. 27 Regulated 5V from USB

PHYSICAL DIMENSIONS (unit: mm)


| SYMBOL | SOT-23-6 | |
|--------|-------------|------|
| | MILLIMETERS | |
| | MIN. | MAX. |
| A | 0.95 | 1.45 |
| A1 | 0.05 | 0.15 |
| A2 | 0.90 | 1.30 |
| b | 0.30 | 0.50 |
| c | 0.08 | 0.22 |
| D | 2.80 | 3.00 |
| E | 2.60 | 3.00 |
| E1 | 1.50 | 1.70 |
| e | 0.95 BSC | |
| e1 | 1.90 BSC | |
| L | 0.30 | 0.60 |
| L1 | 0.60 REF | |
| θ | 0° | 8° |

PART MARKING

PACKING: Moisture sensitivity level MSL3

3000 pcs in antistatic tape on a reel packed in a moisture barrier bag (MBB).

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